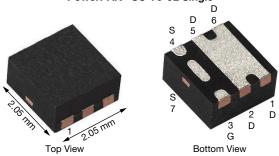
Vishay Siliconix

P-Channel 30 V (D-S) MOSFET

PowerPAK® SC-70-6L Single



p									
PRODUCT SUMMARY									
V _{DS} (V)	-30								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -10 \text{ V}$	0.0265								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0400								
Q _g typ. (nC)	10								
I _D (A) ^a	-12								
Configuration	Single								

FEATURES

- TrenchFET® Gen III p-channel power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
- 100% R_q tested

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

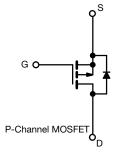


RoHS COMPLIANT

HALOGEN FREE

APPLICATIONS

- Load switch
- DC/DC converters
- · High speed switching
- Power management in battery-operated, mobile and wearable devices



ORDERING INFORMATION						
Package	PowerPAK SC-70					
Lead (Pb)-free and halogen-free	SiA469DJ-T1-GE3					

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	-30	V	
Gate-source voltage		V _{GS}	± 20	v
	T _C = 25 °C		-12 ^a	
Continuous drain surrent /T 150 °C)	T _C = 70 °C	T , 🗀	-12 ^a	
Continuous drain current (T _J = 150 °C)	T _A =25 °C	I _D	-8.8 b, c	
	T _A = 70 °C		_7 b, c	A
Pulsed drain current (t = 100 μs)	I _{DM}	-40		
	T _C = 25 °C		-12 ^a	
Continuous source-drain diode current	T _A = 70 °C	I _S	-2.7 b, c	
	T _C = 25 °C		15.6	
Maximum power dissipation	T _C = 70 °C		10	10/
	T _A = 25 °C	P _D	3.3 b, c	W
	T _A = 70 °C		2.1 ^{b, c}	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	20
Soldering recommendations (peak tempera		260	°C	

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R_{thJA}	30	38	°CAM				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	6.5	8	°C/W				

Notes

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.



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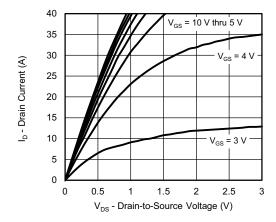
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			•		•	ı
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	-25.5	-	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	7	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-	-3	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zana ala alla adala a mad	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μΑ
Zero gate voltage drain current		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = 0 \text{ V}$	-10	-	-	Α
D	_ ` ′	$V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$	-	0.0210	0.0265	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -3 \text{ A}$	-	0.0300	0.0400	Ω
Forward transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -5 \text{ A}$	-	15	-	S
Dynamic ^b			•	1	•	
Input capacitance	C _{iss}		-	1020	-	
Output capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	130	-	pF
Reverse transfer capacitance	C _{rss}		-	115	-	
Total gate charge	Qg	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5 \text{ A}$	-	21	32	nC
		$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5 \text{ A}$	-	10	15	
Gate-source charge	Q _{gs}	V 45VV 45VV 5A	-	2.3	-	
Gate-drain charge	Q_{gd}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$	-	3.6	-	
Gate resistance	R_g	f = 1 MHz	1.8	9	18	Ω
Turn-on delay time	t _{d(on)}		-	30	60	
Rise time	t _r	$V_{DD} = -15 \text{ V}, R_L = 3 \Omega, I_D \cong -5 \text{ A},$	-	26	50	ns
Turn-off delay time	t _{d(off)}	V_{GEN} = -4.5 V, R_g = 1 Ω	-	25	50	
Fall time	t _f		-	14	30	
Turn-on delay time	t _{d(on)}		-	7	15	
Rise time	t _r	V_{DD} = -15 V, R_L = 3 Ω , $I_D \cong$ -5 A,	-	17	35	
Turn-off delay time	t _{d(off)}	V_{GEN} = -10 V, R_g = 1 Ω	-	30	30	
Fall time	t _f		-	15	30	
Drain-Source Body Diode Characteristi	cs		•		•	
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	-12	
Pulse diode forward current	I _{SM}		-	-	-40	Α
Body diode voltage	V_{SD}	$I_S = -5 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.85	-1.2	V
Body diode reverse recovery time	t _{rr}		-	18	40	ns
Body diode reverse recovery charge	Q _{rr}		-	10	20	nC
Reverse recovery fall time	t _a	$I_F = -5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	10	-	
Reverse recovery rise time	t _b		-	8	_	ns

Notes

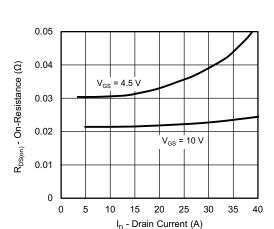
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

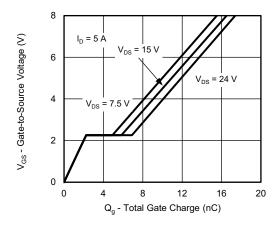




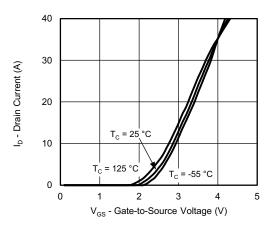
Output Characteristics



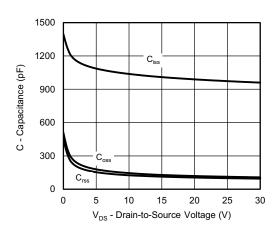
On-Resistance vs. Drain Current and Gate Voltage



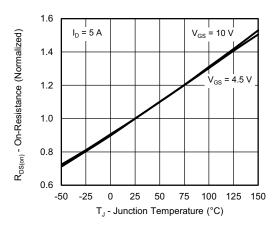
Gate Charge



Transfer Characteristics

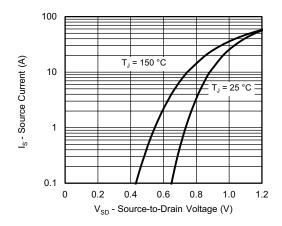


Capacitance

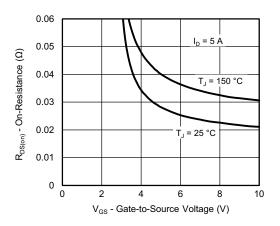


On-Resistance vs. Junction Temperature

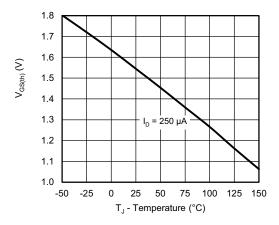




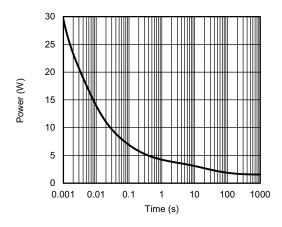
Source-Drain Diode Forward Voltage



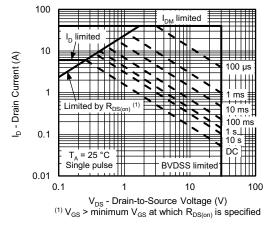
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

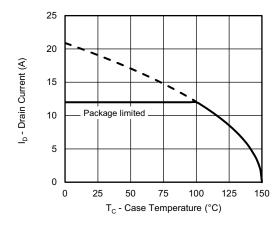


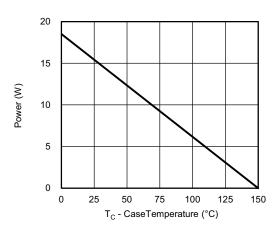
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient







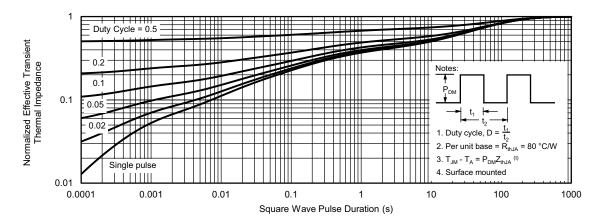
Current Derating a

Power, Junction-to-Case

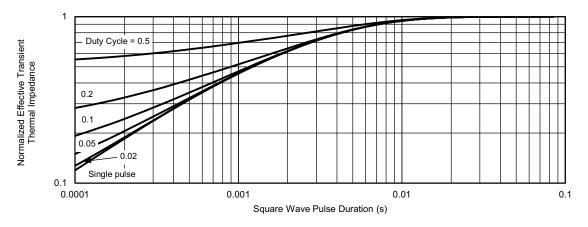
Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

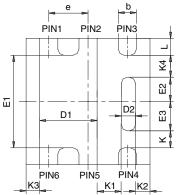
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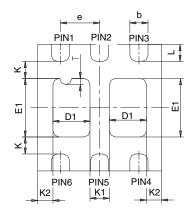




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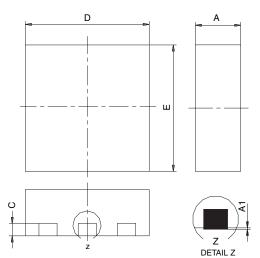
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP			0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP				
К3		0.225 TYP		0.009 TYP						•	•		
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
T							0.05	0.10	0.15	0.002	0.004	0.006	

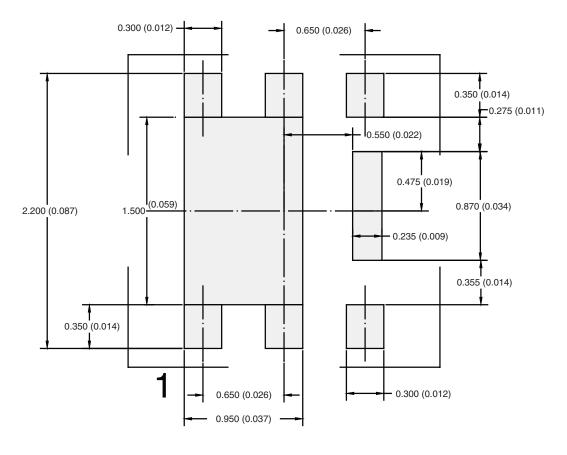
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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